



Emittance Measurement of a Nanostructured Strong-Field Cathode

Gerard Lawler¹, Joshua Mann¹, Nathan Majernik¹, Nathan Montanez¹, Victor Yu², and James Rosenzweig¹ ¹ UCLA, Los Angeles, CA 90095 ² Radiabeam Technologies, Santa Monica, CA







- 1. Motivations & background
- 2. Cathode fabrication
- 3. Characterization incl. emittance measurement
- 4. Future work & conclusions





- National Science Foundation Center for Bright Beams (NSF CBB) exploring limits of electron beam brightness for many applications
 - Free electron lasers, ultrafast electron diffraction, advanced accelerating structures, etc.
- One route to increase initial brightness at cathode via smaller laser spot size
- Particularly here interested in engineering cathodes to reduce area of emission (example of nanotip below)
- Charge extracted small due to damage at higher intensity



A/m⁻-str 1.E+17 Vetallic tips 1.E+15 RF photoiniectors Schottky emitter 1.E+13 otoemission into-field emission 1.E+11 ž 1.E+09 DC photo emissio 1.E+07 1 E - 041 E-02 Current (A)

Quantum limi

From C. Brau

M. Kruger, et al. New Journal of Physics 14, 085019 (2012).







- Inspired by nanotips used for electron microscopy we want to make higher current
- Projected tip forms nanoblade, allowing for higher current extraction based on increased illumination and higher damage threshold from higher laser fluence
- Like nanotip, nanoblade complicated environment where electron scattering process produces high energy emitted electrons







J. Mann, G. Lawler, J. Rosenzweig, *Instruments* **2019**, *3*(4), *59;*





- Nanofabrication here refers procedure to use photolithography and an anisotropic wet etching to produce atomically sharp structures on silicon wafers
- UCLA NanoLab offers unique access to industrial technology to students in an academic environment







- Multi-step cathode recipe continually being refined
 - Produces atomically sharp extendend edge (nanoblade)
 - Then coated by metallic layers to produe cathode
- Success rate for fabrication can be improved
- Each silcon wafer produces approx 30-40 useable cathodes













9/13/2018 HV det mag ⊞ tilt WD 10:21:53 AM 10.00 kV TLD 250 000 x 45 ° 5.1 mm ----- 100 nm -----





- Cathode sample 15mm x 3 mm
- 800 nm, 35 fs pulses, between 10¹² and 10¹³ W/cm² peak, 100 um spot size, polarized normal to blade surface
- Downstream camera for alignment
- Small angle of incidence for full 15 mm blade illumination









- Notable damage directly attributable to laser illumination not common below 10^13 W/cm^2 peak
- Only upon inspection and does not effect long term yield of 10^5 e- per pulse
- Possibly due more to uneven sputtering coating exposing silicon







- Sample location = biased mount containing 8 fixture locations
 - -Currently 4 Au and 4 W (each with double blade geometry)
- After emission electrons can be focused onto MCP and phosphor screen 25cm away via an electrostatic einzel lens
- Advantages such as preserving energy and ease of operation
- Focus of thin line of charge difficult to spatially resolve







- Intentional pitch angle
- Simplified simulation of a monochromatic high aspect ratio beam with 0eV mean transverse energy (MTE)
- Transverse cross section (left)
- Trajectories of corresponding electrons (right)







- Z coordinate of transverse cross section constant @ detector
- Increase the lens strength
- Curves beam more looping around into waist like feature before returning to line like shape





Nonzero Energy Spread



- Bins of energy at emission from 0 to 500 keV
- Voltage on lens to get focus at 25cm
- With 0 eV MTE
- Implicit energy filtering for energies below focusing voltage so bias of cathode holder necessary







- Same simulation now with 5eV MTE added due to apex curvature
- Note blurring effects
- For higher MTE distinct structure not visible
- Implying upper bound on MTE









• Lens scan data data v. 500eV uniform distribution simulation with 5 eV MTE





Beam "Waists"



- Beam waists @ -500V bias and -530V lens voltage
- Simulated 5 eV MTE & uniform distr. 0-1keV
- ϵ_y =136 ± 16 um rad; ϵ_x =13.7 ± 2.7 um rad wiithin 3mm radius
- Additional data for 200, 300, 400, and 800 V bias





- Presence of second blade limiting emittance measurement capability
- Consider reshaping existing cathodes with focused ion beam (FIB)
- Time consuming, 30 minutes to right
- Maybe useful for future plasmonic studies and small linear beamlets









- Beam produced from nanofabricated cathode higher current and robustness than nanotip and measured emittance
- Pattern of nanostructure reflected in beam via high aspect ratio
- Lowering of emittance possible with fabrication modifications or additional steps





Thank You